

Amendments to the Specification:

Please replace paragraph [0038] with the following amended paragraph:

[0038] Next, as shown in Fig. 3D, using deposition, photolithography, and etching, a second metal layer formed on the gate insulating layer 46 forms the pattern of data lines 34a and 34b, the source electrodes S of the TFTs 38a and 38b, and the drain electrodes D of the TFTs 38a and 38b. Preferably, the second metal layer is Cr, Ta, Ti, Al or Mo. Accordingly, the first floating BM shielding layers 42A overlap across the corresponding source electrodes S extension portion of the first data line 34a, which is a part of the source electrodes S of the TFT 38b of an adjacent pixel area.